

**IN THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

1-59(Canceled)

60. (Currently Amended) A method ~~[[for]]~~ of manufacturing a display device comprising the steps of:

forming a plurality of thin film transistors over a substrate;

forming an insulating film comprising a resin over the plurality of thin film transistors;

forming a passivation film over the insulating film; and

forming an electroluminescence element over the passivation film, said electroluminescence element comprising a first electrode formed in contact with the passivation film, a light emitting layer formed ~~[[on]]~~ over the first electrode by an ink jet method and a second electrode formed ~~[[on]]~~ over the light emitting layer,

wherein said first electrode is electrically connected to one of said thin film transistors through a contact hole through said passivation film and said insulating film~~[[.]]~~,

wherein the light emitting layer is in contact with the passivation film.

61. (Canceled)

62. (Currently Amended) A method of manufacturing a display device according to claim 60, wherein the passivation film comprises an insulating film that comprises at least an element selected from a group consisting of B (boron), C (carbon) and N (nitrogen) and an element

selected from a group consisting of Al (aluminum), Si (silicon) and P (phosphorus), or an insulating film that comprises Si, Al, N, O and M where M is a rare earth element preferably one selected from a group consisting of Ce (cerium), Yb (ytterbium), Sm (samarium), Er (erbium), Y (yttrium), La (lanthanum), Gd (gadolinium), Dy (dysprosium) and Nd (neodymium).

63. (Currently Amended) A method of manufacturing a display device according to claim 60, wherein said passivation film comprises a material selected from the group consisting of silicon nitride and silicon oxynitride.

64. (Currently Amended) A method of manufacturing a display device according to claim 60, wherein said light emitting layer electroluminescence material comprises an organic light emitting layer.

65. (Currently Amended) A method ~~[[for]]~~ of manufacturing a display device comprising the steps of:

forming a plurality of thin film transistors over a substrate;

forming an insulating film comprising a resin over the plurality of thin film transistors;

forming a first passivation film over the insulating film;

forming an electroluminescence element over the first passivation film, said electroluminescence element comprising a first electrode formed in contact with the first passivation film, a second electrode and a light emitting layer interposed therebetween; and

forming a second passivation film over the electroluminescence element,

wherein the light emitting layer, the second electrode and the second passivation film are formed in succession without exposure to an atmosphere, and

~~wherein the electroluminescence element is interposed between the first passivation film and the second passivation film.~~

66. (Canceled)

67. (Currently Amended) A method of manufacturing a display device according to claim 65, wherein each of the first passivation film and the second passivation film comprises at least an element selected from a group consisting of B (boron), C (carbon) and N (nitrogen) and an element selected from a group consisting of Al (aluminum), Si (silicon) and P (phosphorus).

68. (Currently Amended) A method of manufacturing a display device according to claim 65, wherein each of the first passivation film and the second passivation film comprises Si, Al, N, O and M where M is a rare earth element preferably one selected from a group consisting of Ce (cerium), Yb (ytterbium), Sm (samarium), Er (erbium), Y (yttrium), La (lanthanum), Gd (gadolinium), Dy (dysprosium) and Nd (neodymium).

69. (Currently Amended) A method of manufacturing a display device according to claim 65, further comprising a step of forming an insulating film that comprises at least an element selected from a group consisting of B (boron), C (carbon) and N (nitrogen) and an element selected from a group consisting of Al (aluminum), Si (silicon) and P (phosphorus), between the substrate and the plurality of thin film transistors.

70. (Currently Amended) A method of manufacturing a display device according to claim 65, further comprising a step of forming an insulating film that comprises Si, Al, N, O and

M where M is a rare earth element preferably one selected from a group consisting of Ce (cerium), Yb (ytterbium), Sm (samarium), Er (erbium), Y (yttrium), La (lanthanum), Gd (gadolinium), Dy (dysprosium) and Nd (neodymium), between the substrate and the plurality of thin film transistors.

71. (Currently Amended) A method ~~[[for]]~~ of manufacturing a display device comprising the steps of:

forming a plurality of thin film transistors over a substrate;  
forming a leveling film comprising a resin over the plurality of thin film transistors;  
forming a passivation film over the leveling film; and  
forming an electroluminescence element over the passivation film, said electroluminescence element comprising a first electrode formed in contact with the passivation film, a second electrode and a light emitting layer interposed therebetween,

wherein the light emitting layer is formed by an ink jet method so as to be in contact with the passivation film.

72. (Canceled)

73. (Currently Amended) A method of manufacturing a display device according to claim 71, wherein said passivation film comprises a material selected from the group consisting of silicon nitride and silicon oxynitride.

74. (Currently Amended) A method of manufacturing a display device according to claim 71, wherein said light emitting layer ~~electroluminescence material~~ comprises an organic light emitting layer.

75. (Currently Amended) A method of manufacturing a display device comprising the steps of:

forming a thin film transistor over a substrate;

forming a first insulating film comprising silicon and nitrogen over the thin film transistor;

forming a leveling film comprising a resin over the first insulating film;

forming a second insulating film comprising silicon nitride;

forming a light emitting element over the second insulating film, said light emitting element comprising a first electrode formed in contact with the second insulating film, a second electrode and a light emitting layer ~~comprising an organic material~~ interposed therebetween; and

forming a third insulating film comprising a material selected from the group consisting of aluminum nitride, silicon carbide, silicon nitride, boron nitride, boron phosphate and aluminum oxide,

wherein the light emitting layer, the second electrode and the third insulating film are formed in succession without exposure to an atmosphere.

76. (Currently Amended) A display device comprising:

a substrate;

a thin film transistor formed over the substrate, said thin film transistor comprising at least a semiconductor film and a gate electrode adjacent to the semiconductor film with a gate insulating film therebetween;

a first insulating film ~~comprising silicon, nitrogen and oxygen~~ formed over at least the semiconductor film and the gate electrode;

a leveling film comprising a resin formed over the first insulating film;

a second insulating film ~~comprising silicon nitride~~ formed ~~[[on]]~~ over the leveling film;

a light emitting element formed ~~[[on]]~~ over the second insulating film, said light emitting element comprising a first electrode formed in contact with the second insulating film, an electroluminescence layer ~~comprising an organic material~~ over the first electrode and a second electrode formed over the electroluminescence layer; and

a third insulating film formed over the second electrode, ~~said third insulating film comprising a material selected from the group consisting of aluminum nitride, silicon carbide, silicon nitride, boron nitride, boron phosphate and aluminum oxide.~~

wherein the electroluminescence layer is in contact with the second insulating film.

77. (Canceled)

78. (Previous Presented) A display device according to claim 76, wherein a storage capacitor is formed by the semiconductor film, the gate insulating film and a capacitor electrode.

79. (New) A display device according to claim 76, wherein the first insulating film comprises silicon, nitrogen and oxygen.

80. (New) A display device according to claim 76, wherein the second insulating film comprises silicon nitride.

81. (New) A display device according to claim 76, wherein the third insulating film comprises a material selected from the group consisting of aluminum nitride, silicon carbide, silicon nitride, boron nitride, boron phosphate and aluminum oxide.